

REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Changes made to Table 1, updated paragraph 4.4.1f, and editorial changes throughout. ksr	03-02-21	Raymond Monnin
B	Constant acceleration changed for class Q and V to condition B for case outline Y and remains condition D for devices built with case outline X. ksr	03-09-08	Raymond Monnin
C	Added T _R and T _F to section 1.4, and updated boilerplate paragraphs. ksr	04-01-04	Raymond Monnin
D	Added devices 05 – 08; Update to 1.3, made changes to IIL and IOZ in Table I, made change to paragraph 4.2.2 and 4.4.1f, and updated boilerplate paragraphs. ksr	04-08-27	Raymond Monnin
E	Editorial changes to paragraphs 4.3 and 4.4. ksr	05-09-29	Raymond Monnin
F	Boilerplate update, part of 5 year review. ksr	10-11-15	Charles F. Saffle
G	Added device types 09 and 10 to section 1.2.2 and Table I. Added additional testing criteria for devices 09 and 10 in 4.4.2.2 and 4.4.5. Removed reference to vendor internal document in 4.4.1f(2). Removed reference to vendor software in 4.6. Removed vendor website URL from 6.7. Updated boilerplate to current requirements. lhl	12-05-21	Charles F. Saffle
H	Updated boilerplate to current requirements. Removed references to Class M. Section 4.2.2 is now 4.2.1. Updated 4.2.1f for device types 09 and 10. lhl	12-11-26	Charles F. Saffle
J	Updated boilerplate to current requirements. Updated section 4.2.1f(6) for device types 09 and 10. lhl	14-01-06	Charles F. Saffle

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REV																				
SHEET																				
REV	J	J	J	J	J	J	J	J												
SHEET	15	16	17	18	19	20	21	22												
REV STATUS				REV			J	J	J	J	J	J	J	J	J	J	J	J	J	
OF SHEETS				SHEET			1	2	3	4	5	6	7	8	9	10	11	12	13	14

PMIC N/A	PREPARED BY Kenneth Rice			<p align="center">DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990 http://www.landandmaritime.dla.mil</p> <p align="center">MICROCIRCUIT, MEMORY, DIGITAL, CMOS, FIELD PROGRAMMABLE GATE ARRAY, 72,000 GATES, MONOLITHIC SILICON</p>																
<p align="center">STANDARD MICROCIRCUIT DRAWING</p> <p align="center">THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p> <p align="center">AMSC N/A</p>	CHECKED BY Raj Pithadia																			
	APPROVED BY Raymond Monnin																			
	DRAWING APPROVAL DATE 02 - 02 - 25																			
REVISION LEVEL J			SIZE A	CAGE CODE 67268	5962-01515															
			SHEET 1 OF 22																	

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
X	See figure 1	256	Ceramic Quad Flat Pack
Y	See figure 1	208	Ceramic Quad Flat Pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

1.3 Absolute maximum ratings (for 2.5V/3.3V/5.0V operating conditions). 8/

DC supply voltage range (V_{CCI})	-0.3 to +6.0 V dc
DC supply voltage range (V_{CCA})	-0.3 to +3.0 V dc
Input voltage range (V_i)	-0.5 to +6.0 V dc
Input voltage(V_i) for bi-directional I/Os when using 3.3V PCI	-0.5 to ($+V_{CCI} + 0.5$) V dc
Output voltage range (V_o)	-0.5 to ($+V_{CCI} + 0.5$) V dc
Storage temperature range (V_{STG})	-65 °C to +150 °C
Lead temperature (soldering, 10 seconds)	300 °C
Thermal resistance, junction-to-case (θ_{JC} for Case X and Y)	0.5 °C/W
Maximum junction temperature (T_J)	150 °C

1.4 Recommended operating conditions.

3.3V power supply voltage range	3.0 to 3.6 V dc ($\pm 10\% V_{CCI}$)
5.0V power supply voltage range	4.5 to 5.5 V dc ($\pm 10\% V_{CCI}$)
2.5V power supply voltage range	2.25 to 2.75 V dc ($\pm 10\% V_{CCA}$)
Case operating temperature range (T_c)	-55 °C to +125 °C
Input transition time T_R and T_F	10 ns 9/

1.5 Digital logic testing for device classes Q and V.

Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012)	100 percent 10/
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2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

8/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

9/ If T_R and T_F exceeds the limit of 10 ns, the device manufacturer cannot guarantee device functionality.

10/ 100 percent test coverage of blank programmable logic devices.

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DEPARTMENT OF DEFENSE HANDBOOKS

- MIL-HDBK-103 - List of Standard Microcircuit Drawings.
- MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <http://quicksearch.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DoDISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DoDISS are the issues of the documents cited in the solicitation.

JEDEC INTERNATIONAL (JEDEC)

JEDEC JESD 78 - IC Latch-Up Test.

(Copies of this document are available online at www.jedec.org/ or from JEDEC, 3103 North 10th Street, Suite 240-S, Arlington, VA 22201)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents also may be available in or through libraries or other informational services.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein and figure 1.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.

3.2.3 Truth table(s).

3.2.3.1 Unprogrammed devices. The truth table or test vectors for unprogrammed devices for contracts involving no altered item drawing is not part of this drawing. When required in screening (see 4.2 herein) or qualification conformance inspection, groups A, B, C, D, or E (see 4.4 herein), the devices shall be programmed by the manufacturer prior to test. A minimum of 90 percent of the total number of logic modules shall be utilized or at least 25 percent of the total logic modules shall be utilized for any altered item drawing pattern.

3.2.3.2 Programmed devices. The truth table or test vectors for programmed devices shall be as specified by an attached altered item drawing.

3.2.4 Switching test circuit and waveforms. The switching test circuit and waveforms diagram shall be as specified on figure 3.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

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3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.

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TABLE I. Electrical performance characteristics. 1/ 2/

Operation with $V_{CCI} = 3.3V$ or $V_{CCI} = 5.0V$ (for 3.3V LVTTTL and 5V TTL I/O Operations)

Test	Symbol	Conditions 3/ 2.25 V ≤ V _{CCA} ≤ 2.75 V 3.0 V ≤ V _{CCI} ≤ 3.6 V or 4.5 V ≤ V _{CCI} ≤ 5.5 V -55°C ≤ T _C ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
High level output voltage	V _{OH}	I _{OH} = -1mA, V _{CCI} = Min., V _I = V _{IH} or V _{IL}	1,2,3	All	0.9 * V _{CCI}	V _{CCI}	V
		I _{OH} = -8mA V _{CCI} = Min. V _I = V _{IH} or V _{IL}			2.4	V _{CCI}	
Low level output voltage	V _{OL}	I _{OL} = 1mA V _{CCI} = Min. V _I = V _{IH} or V _{IL}	1,2,3	All		0.1 * V _{CCI}	V
		I _{OL} = 12mA V _{CCI} = Min. V _I = V _{IH} or V _{IL}				0.4	
Low level input voltage	V _{IL}		1,2,3	All		0.8	V
High level input voltage	V _{IH}		1,2,3	All	2.0		V
Input leakage current	I _{IL}	V _{IN} = V _{CCI} or GND	1,2,3	01,02, 03,04	-20	20	μA
		V _{IN} = V _{CCI} or GND and 4.5 V ≤ V _{CCI} ≤ 5.25 V		05,06,07, 08,09,10	-20	20	μA
		V _{IN} = V _{CCI} or GND and 5.25 V < V _{CCI} ≤ 5.5 V		05,06,07, 08,09,10	-70	70	μA
3-state output leakage current	I _{oz}	V _{OUT} = V _{CCI} or GND	1,2,3	01,02, 03,04	-20	20	μA
		V _{IN} = V _{CCI} or GND and 4.5 V ≤ V _{CCI} ≤ 5.25 V		05,06,07, 08,09,10	-20	20	μA
		V _{IN} = V _{CCI} or GND and 5.25 V < V _{CCI} ≤ 5.5 V		05,06,07, 08,09,10	-70	70	μA
I/O terminal capacitance	C _{I/O} & C _{CLK}	See 4.4.1c f ≤ 1.0 MHz, V _{OUT} ≈ 0 V	4	All		20	pF
Standby supply current	I _{CC} 4/		1,2,3	All		25	mA
Functional tests	FT 5/	See 4.4.1e	7,8A,8B	All			
Binning circuit delay	t _{PBLH} , t _{PBHL} 6/ 7/	See figure 3, V _{IH} = 3.0 V, V _{IL} = 0 V, V _{OUT} = 1.5 V, V _{CCA} = 2.5 V, V _{CCI} = 3.3 V	9	01,03, 05,07,09		107	ns
				02,04, 06,08,10		91	

See notes at end of Table I.

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TABLE I. Electrical performance characteristics – Continued. 1/ 2/

Operation with $V_{CC1} = 5.0V$ (for 5V CMOS I/O Operations)

Test	Symbol	Conditions <u>3/</u> $2.25 V \leq V_{CCA} \leq 2.75 V$ $4.5 V \leq V_{CC1} \leq 5.5 V$ $-55^{\circ}C \leq T_C \leq +125^{\circ}C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
High level output voltage	V_{OH}	$V_{CC1} = \text{Min.},$ $V_I = V_{CC1} \text{ or GND}$ $I_{OH} = -20\mu A$	1,2,3	All	$V_{CC1} - 0.1$		V
Low level output voltage	V_{OL}	$V_{CC1} = \text{Min.},$ $V_I = V_{CC1} \text{ or GND}$ $I_{OL} = +20 \mu A$	1,2,3	All		0.1	V
Low level input voltage	V_{IL}	$V_{OUT} \leq V_{VOL}(\text{Max})$	1,2,3	All		$0.3 * V_{CC1}$	V
High level input voltage	V_{IH}	$V_{OUT} \geq V_{VOH}(\text{Max})$	1,2,3	All	$0.7 * V_{CC1}$		V
3-state output leakage current	I_{OZ}	$V_{OUT} = V_{CC1} \text{ or GND}$	1,2,3	01,02, 03,04	-20	20	μA
		$V_{IN} = V_{CC1} \text{ or GND and}$ $4.5 V \leq V_{CC1} \leq 5.25 V$		05,06, 07,08, 09,10	-20	20	μA
		$V_{IN} = V_{CC1} \text{ or GND and}$ $5.25 V < V_{CC1} \leq 5.5 V$		05,06, 07,08, 09,10	-70	70	μA
I/O terminal capacitance	$C_{I/O}$ & C_{CLK}	See 4.4.1c $f \leq 1.0 \text{ MHz}, V_{OUT} \approx 0 V$	4	All		20	pF
Standby supply current	I_{CC} <u>4/</u>		1,2,3	All		25	mA
Functional tests	FT <u>5/</u>	See 4.4.1e	7,8A,8B	All			

See notes at end of Table I.

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TABLE I. Electrical performance characteristics – Continued. 1/ 2/

Operation with $V_{CCI} = 5.0V$ (for 5.0V PCI I/O Operations, 8/)

Test	Symbol	Conditions <u>3/</u> $2.25 V \leq V_{CCA} \leq 2.75 V$ $4.5 V \leq V_{CCI} \leq 5.5 V$ $-55^{\circ}C \leq T_C \leq +125^{\circ}C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
High level input voltage	V_{IH}		1,2,3	All	2.0	$V_{CCI} + 0.5$	V
Low level input voltage	V_{IL}		1,2,3	All	-0.5	0.8	V
Input high leakage current	I_{IH}	$V_{IN} = 2.75 V$	1,2,3	All		70	μA
Input low leakage current	I_{IL}	$V_{IN} = 0.5 V$	1,2,3	All		-70	μA
High level output voltage	V_{OH}	$I_{OUT} = -2mA$	1,2,3	All	2.4		V
Low level output voltage	V_{OL} <u>9/</u>	$I_{OUT} = 3mA, 6mA$	1,2,3	All		0.55	V
Input pin capacitance	C_{IN} <u>10/</u>		4	All		10	pF
Clock pin capacitance	C_{CLK} <u>10/</u>		4	All	5	12	pF

See notes at the end of Table I.

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TABLE I. Electrical performance characteristics – Continued. 1/ 2/

Operation with $V_{CCI} = 3.3V$ (for 3.3V PCI I/O Operations, 8/)

Test	Symbol	Conditions 3/ 2.25 V ≤ V _{CCA} ≤ 2.75 V 3.0 V ≤ V _{CCI} ≤ 3.6 V -55°C ≤ T _C ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
High level input voltage	V _{IH}		1,2,3	All	0.5 * V _{CCI}	V _{CCI} +0.5	V
Low level input voltage	V _{IL}		1,2,3	All	-0.5	0.3 * V _{CCI}	V
Input pull-up voltage	I _{IPU} 11/		1,2,3	All	0.7 * V _{CCI}		V
Input leakage current	I _{IH} / I _{IL}	0 ≤ V _{IN} ≤ V _{CCI}	1,2,3	All	-20	20	μA
High level output voltage	V _{OH}	I _{OUT} = -500 μA	1,2,3	All	0.9 * V _{CCI}		V
Low level output voltage	V _{OL}	I _{OUT} = 1500 μA	1,2,3	All		0.1 * V _{CCI}	V
Input pin capacitance	C _{IN} 10/		4	All		10	pF
Clock pin capacitance	C _{CLK} 10/		4	All	5	12	pF

- 1/ AC/Timing parameters (subgroup 9, 10, 11) are not directly tested but fully characterized (see note 2/), which are published on device manufacturer's data sheet and implemented in manufacturer's software (see 6.7 and Table IIA note 8/ herein).
- 2/ Characterization data is taken at initial device introduction and repeated after any design or process changes that may affect the related parameters. Devices are first 100 percent functionally tested, then benchmark design/timing patterns are programmed into the devices and then characterized to determine the compliance of the parameters.
- 3/ All tests shall be performed under the worst-case condition unless otherwise specified.
- 4/ Standby I_{CC} is the total standby current of I_{CCA} and I_{CCI}.
- 5/ Devices are functionally tested using a serial scan test method. Data is shifted into the TDI pin and the TCK pin is used as a clock. The data is used to drive the inputs of the internal logic and I/O modules, allowing a complete functional test to be performed. The outputs of the module can be read by shifting out the output response or by monitoring the PRA, PRB, or TDO pins.
- 6/ Binning circuit delay is defined as the input-to-output delay of a special path called the "binning circuit". The binning circuit consists of one input buffer plus a fixed number of combinatorial logic modules plus an output buffer. These modules are configured as non-inverting buffers and are connected through programmed antifuses with typical capacitive loading.
- 7/ Binning circuit parameters are tested with typical conditions as listed in this table at room temperature only. Measurement of binning circuit propagation delay may be used to distinguish standard and -1 speed devices. However, the performance of user designs are mainly affected by variations introduced in individual designs. Therefore, measurement difference in binning circuit speed shall not be used for picking faster devices from devices of the same speed grade.
- 8/ This device is electrically compliant with the PCI Local Bus Specification Rev. 2.2.
- 9/ Signals without pull-up resistors must have 3 mA low output current. Signals requiring pull-up must have 6 mA; the latter includes FRAME#, IRDY#, TRDY#, DEVSEL#, STOP#, SERR#, PERR#, LOCK#, and, when used AD[63::32], C/BE[7::4]#, PAR64, REQ64#, and ACK64#.

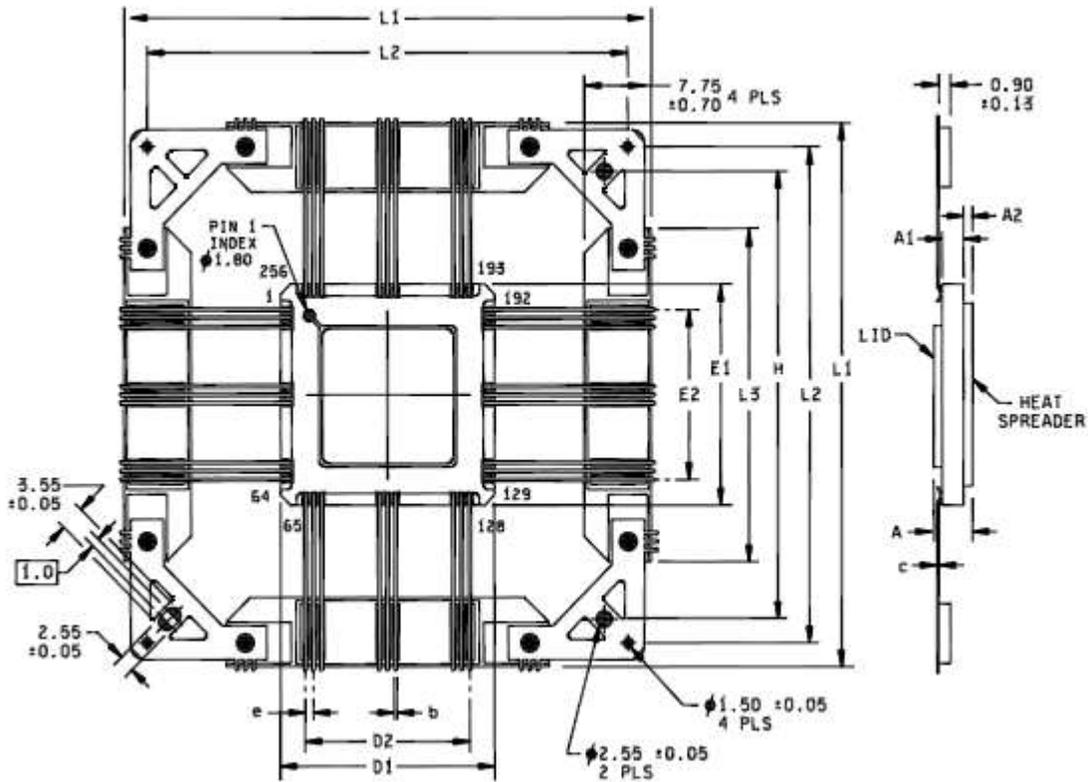
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TABLE I. Electrical performance characteristics – Continued. 1/ 2/

- 10/ Absolute maximum pin capacitance for a PCI input is 10 pF. Exceptions will be for clock pins including CLK A/B, HCLK, QCLK A/B/C/D.
- 11/ This parameter (I_{IPU}) is not directly tested but fully characterized (see 2/). It is the minimum voltage to which pull-up resistors are calculated to pull a floated network. Applications sensitive to static power utilization should assure that the input buffer is conducting minimum current at this input voltage.

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Case Outline X



NOTES:

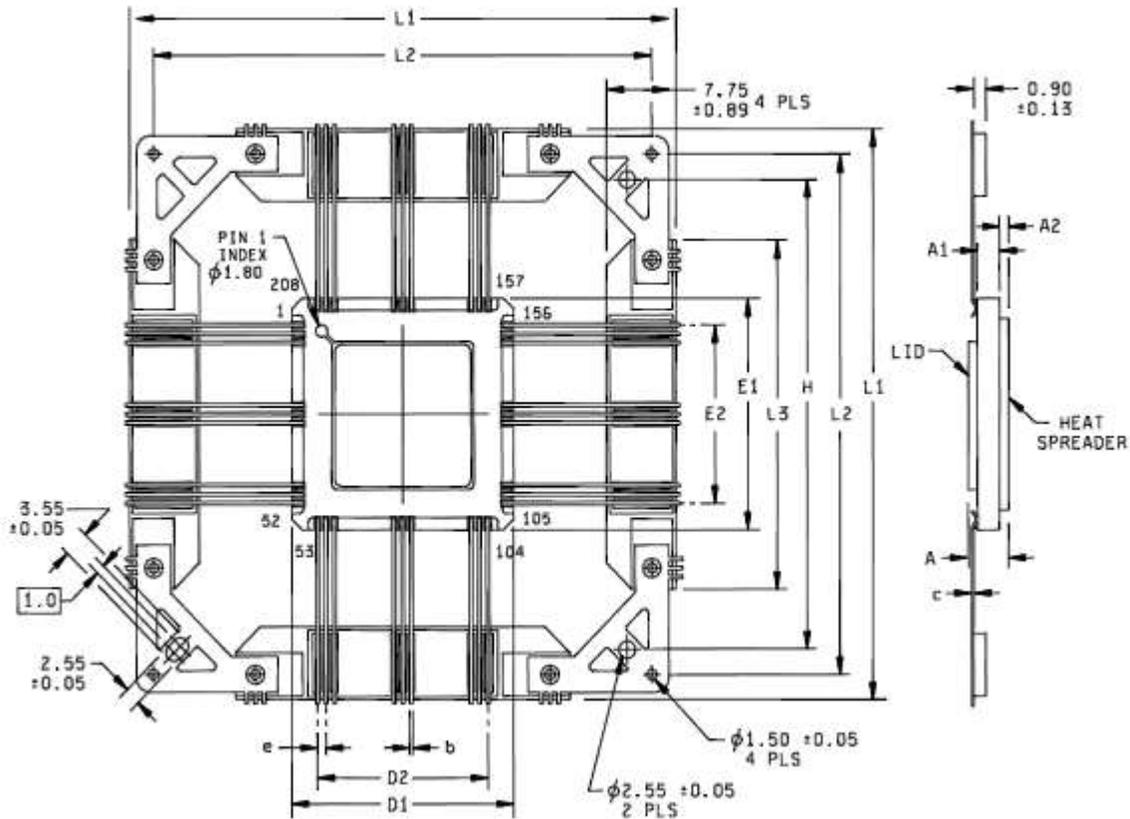
1. All exposed metallized areas and leads are gold plated 100 microinches (2.5 μm) minimum thickness over 80 to 350 microinches (2.0 to 8.9 μm) thickness of nickel
2. Seal ring area is connected to GND.
3. Die attach pad is connected to GND.
4. 20.2 gm of approximated weight is measured after tie-bar removed.
5. Tie-bar dimensions are for reference only.
6. Case outline X includes a large CuW heat spreader at the bottom of the package, which can not be penetrated by X-ray. The CuW heat spreader is connected to GND.

Symbol	Dimension (unit : mm)		
	Min.	Norm.	Max.
A	2.82	3.36	3.90
A1	2.03	2.29	2.55
A2	0.37	0.50	0.63
b	0.18	0.20	0.23
c	0.10	0.15	0.18
D1/E1	35.64	36.00	36.36
D2/E2	31.50 BSC		
e	0.50 BSC		
L1	74.60	75.00	75.40
L2	70.00 BSC		
L3	56.30		
H	65.90 BSC		

FIGURE 1. Case outline.

<p>STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990</p>	<p>SIZE A</p>		<p>5962-01515</p>
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Case Outline Y



NOTES:

1. All exposed metalized areas and leads are gold plated 100 microinches (2.5 μm) minimum thickness over 80 to 350 microinches (2.0 to 8.9 μm) thickness of nickel.
2. Seal ring area is connected to GND.
3. Die attach pad is connected to GND.
4. 18.5 gm approximated weight is measured after tie-bar removed.
5. Tie-bar dimensions are for reference only.
6. Case outline Y includes a large CuW heat spreader at the bottom of the package, which can not be penetrated by X-ray. The CuW heat spreader is connected to GND.

Symbol	Dimension (unit : mm)		
	Min.	Norm.	Max.
A	2.82	3.36	3.90
A1	2.03	2.29	2.55
A2	0.37	0.50	0.63
b	0.18	0.20	0.23
c	0.10	0.15	0.20
D1/E1	28.96	29.21	29.46
D2/E2	25.50 BSC		
e	0.50 BSC		
L1	74.60	75.00	75.40
L2	70.00 BSC		
L3	56.30		
H	65.90 BSC		

FIGURE 1. Case outline. – Continued.

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Case Outline X

Device Types	All	Device Types	All	Device Types	All
Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol
1	GND	44	I/O	87	I/O
2	TDI, I/O	45	I/O	88	I/O
3	I/O	46	VCCA	89	QCLKA, I/O
4	I/O	47	VCCI	90	PRB, I/O
5	I/O	48	I/O	91	GND
6	I/O	49	I/O	92	VCCI
7	I/O	50	I/O	93	GND
8	I/O	51	I/O	94	VCCA
9	I/O	52	I/O	95	I/O
10	I/O	53	I/O	96	HCLK
11	TMS	54	I/O	97	I/O
12	I/O	55	I/O	98	QCLKB, I/O
13	I/O	56	GND	99	I/O
14	I/O	57	I/O	100	I/O
15	I/O	58	I/O	101	I/O
16	I/O	59	GND	102	I/O
17	VCCI	60	I/O	103	I/O
18	I/O	61	I/O	104	I/O
19	I/O	62	I/O	105	I/O
20	I/O	63	I/O	106	I/O
21	I/O	64	I/O	107	I/O
22	I/O	65	I/O	108	I/O
23	I/O	66	I/O	109	I/O
24	I/O	67	I/O	110	GND
25	I/O	68	I/O	111	I/O
26	I/O	69	I/O	112	I/O
27	I/O	70	I/O	113	I/O
28	VCCI	71	I/O	114	I/O
29	GND	72	I/O	115	I/O
30	VCCA	73	VCCI	116	I/O
31	GND	74	I/O	117	I/O
32	I/O	75	I/O	118	I/O
33	I/O	76	I/O	119	I/O
34	TRSTB	77	I/O	120	VCCI
35	I/O	78	I/O	121	I/O
36	VCCA	79	I/O	122	I/O
37	GND	80	I/O	123	I/O
38	I/O	81	I/O	124	I/O
39	I/O	82	I/O	125	I/O
40	I/O	83	I/O	126	TDO, I/O
41	I/O	84	I/O	127	I/O
42	I/O	85	I/O	128	GND
43	I/O	86	I/O	129	I/O

FIGURE 2. Terminal connections.

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Case Outline X – Continued.

Device Types	All	Device Types	All	Device Types	All
Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol
130	I/O	173	I/O	216	I/O
131	I/O	174	VCCA	217	I/O
132	I/O	175	GND	218	QCLKD, I/O
133	I/O	176	GND	219	CLKA, I/O
134	I/O	177	I/O	220	CLKB, I/O
135	I/O	178	I/O	221	VCCI
136	I/O	179	I/O	222	GND
137	I/O	180	I/O	223	NC
138	I/O	181	I/O	224	GND
139	I/O	182	I/O	225	PRA, I/O
140	I/O	183	VCCI	226	I/O
141	VCCA	184	I/O	227	I/O
142	VCCI	185	I/O	228	VCCA
143	GND	186	I/O	229	I/O
144	VCCA	187	I/O	230	I/O
145	I/O	188	I/O	231	QCLKC, I/O
146	I/O	189	GND	232	I/O
147	I/O	190	I/O	233	I/O
148	I/O	191	I/O	234	I/O
149	I/O	192	I/O	235	I/O
150	I/O	193	I/O	236	I/O
151	I/O	194	I/O	237	I/O
152	I/O	195	I/O	238	I/O
153	I/O	196	I/O	239	I/O
154	I/O	197	I/O	240	GND
155	I/O	198	I/O	241	I/O
156	I/O	199	I/O	242	I/O
157	I/O	200	I/O	243	I/O
158	GND	201	I/O	244	I/O
159	NC	202	VCCI	245	I/O
160	GND	203	I/O	246	I/O
161	VCCI	204	I/O	247	I/O
162	VCCA	205	I/O	248	I/O
163	I/O	206	I/O	249	VCCI
164	I/O	207	I/O	250	I/O
165	I/O	208	I/O	251	I/O
166	I/O	209	I/O	252	I/O
167	I/O	210	I/O	253	I/O
168	I/O	211	I/O	254	I/O
169	I/O	212	I/O	255	I/O
170	I/O	213	I/O	256	TCK, I/O
171	I/O	214	I/O		
172	I/O	215	I/O		

FIGURE 2. Terminal connections. – Continued.

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Case Outline Y

Device Types	All	Device Types	All	Device Types	All
Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol
1	GND	36	I/O	71	I/O
2	TDI, I/O	37	I/O	72	I/O
3	I/O	38	I/O	73	I/O
4	I/O	39	I/O	74	QCLKA, I/O
5	I/O	40	VCCI	75	I/O
6	I/O	41	VCCA	76	PRB, I/O
7	I/O	42	I/O	77	GND
8	I/O	43	I/O	78	VCCA
9	I/O	44	I/O	79	GND
10	I/O	45	I/O	80	NC
11	TMS	46	I/O	81	I/O
12	VCCI	47	I/O	82	HCLK
13	I/O	48	I/O	83	VCCI
14	I/O	49	I/O	84	QCLKB, I/O
15	I/O	50	I/O	85	I/O
16	I/O	51	I/O	86	I/O
17	I/O	52	GND	87	I/O
18	GND	53	I/O	88	I/O
19	VCCA	54	I/O	89	I/O
20	I/O	55	I/O	90	I/O
21	I/O	56	I/O	91	I/O
22	I/O	57	I/O	92	I/O
23	I/O	58	I/O	93	I/O
24	I/O	59	I/O	94	I/O
25	I/O	60	VCCI	95	I/O
26	GND	61	I/O	96	I/O
27	VCCA	62	I/O	97	I/O
28	GND	63	I/O	98	VCCI
29	I/O	64	I/O	99	I/O
30	TRSTB	65	I/O	100	I/O
31	I/O	66	I/O	101	I/O
32	I/O	67	I/O	102	I/O
33	I/O	68	I/O	103	TDO, I/O
34	I/O	69	I/O	104	I/O
35	I/O	70	I/O	105	GND

FIGURE 2. Terminal connections. – Continued.

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Case Outline Y – Continued.

Device Types	All	Device Types	All	Device Types	All
Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol	Terminal Number	Terminal Symbol
106	I/O	141	I/O	176	I/O
107	I/O	142	I/O	177	I/O
108	I/O	143	I/O	178	QCLKD, I/O
109	I/O	144	I/O	179	I/O
110	I/O	145	VCCA	180	CLKA, I/O
111	I/O	146	GND	181	CLKB, I/O
112	I/O	147	I/O	182	NC
113	I/O	148	VCCI	183	GND
114	VCCA	149	I/O	184	VCCA
115	VCCI	150	I/O	185	GND
116	GND	151	I/O	186	PRA, I/O
117	VCCA	152	I/O	187	VCCI
118	I/O	153	I/O	188	I/O
119	I/O	154	I/O	189	I/O
120	I/O	155	I/O	190	QCLKC, I/O
121	I/O	156	I/O	191	I/O
122	I/O	157	GND	192	I/O
123	I/O	158	I/O	193	I/O
124	I/O	159	I/O	194	I/O
125	I/O	160	I/O	195	I/O
126	I/O	161	I/O	196	I/O
127	I/O	162	I/O	197	I/O
128	I/O	163	I/O	198	I/O
129	GND	164	VCCI	199	I/O
130	VCCA	165	I/O	200	I/O
131	GND	166	I/O	201	VCCI
132	I/O	167	I/O	202	I/O
133	I/O	168	I/O	203	I/O
134	I/O	169	I/O	204	I/O
135	I/O	170	I/O	205	I/O
136	I/O	171	I/O	206	I/O
137	I/O	172	I/O	207	I/O
138	I/O	173	I/O	208	TCK, I/O
139	I/O	174	I/O		
140	I/O	175	I/O		

FIGURE 2. Terminal connections. – Continued.

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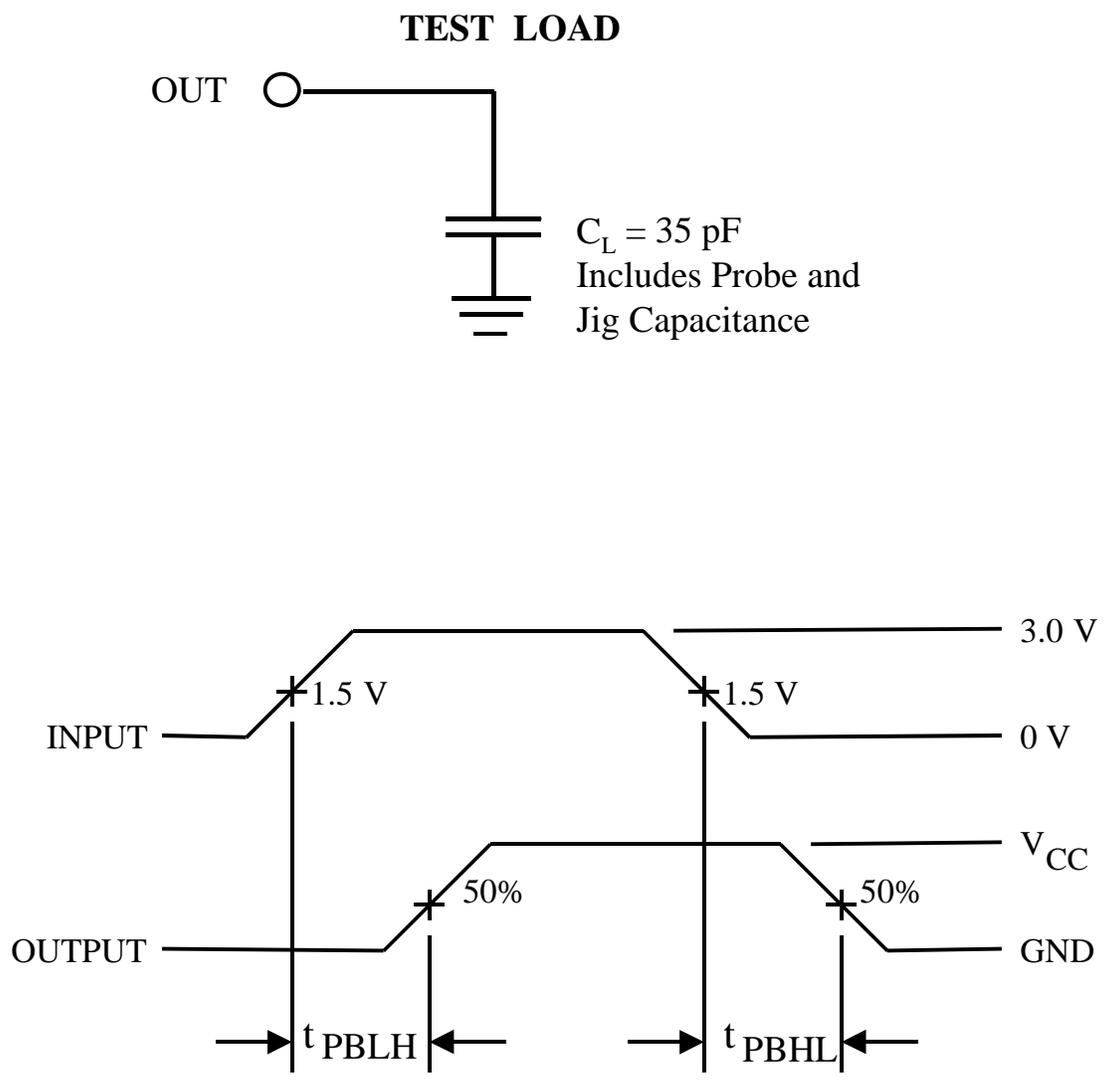


FIGURE 3. Switching test circuit and waveforms. 1/

1/ Loading for 3.3 V PCI is 10 pF and 5 V PCI is 50 pF.

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4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

TABLE IIA. Electrical test requirements. 1/ 2/ 3/ 4/ 5/ 6/ 7/ 8/

Line no.	Test requirements	Subgroups (in accordance with MIL-PRF-38535, table III)	
		Device class Q	Device class V
1	Interim electrical parameters (see 4.2)	1, 7, 9	1, 7, 9
2	Static burn-in (method 1015)	Not required	Required
3	Same as line 1		1*Δ, 7*
4	Dynamic burn-in (method 1015)	Required	Required
5	Same as line 1		1*Δ, 7*
6	Final electrical parameters (see 4.2)	1*, 2, 3, 7*, 8A, 8B, 9	1*, 2, 3, 7*, 8A, 8B, 9
7	Group A test requirement (see 4.4)	1, 2, 3, 4**, 7, 8A, 8B, 9	1, 2, 3, 4**, 7, 8A, 8B, 9
8	Group C end-point electrical parameters (see 4.4)	1, 2, 3, 7, 8A, 8B, 9, 10, 11	1Δ, 2, 3, 7, 8A, 8B, 9, 10, 11
9	Group D end-point electrical parameters (see 4.4)	1, 2, 3, 7, 8A, 8B, 9, 10, 11	1, 2, 3, 7, 8A, 8B, 9, 10, 11
10	Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9

1/ Blank spaces indicate tests are not applicable.

2/ Any or all subgroups may be combined when using high-speed testers.

3/ Subgroups 7 and 8 functional tests shall verify the functionality for unprogrammed devices or that the altered item drawing pattern exists for programmed devices.

4/ * indicates PDA applies to subgroups 1 and 7.

5/ ** see 4.4.1c.

6/ Δ indicates delta limit (see table IIB) shall be required, and the delta values shall be computed with reference to the previous interim electrical parameters.

7/ See 4.4.1d.

8/ Subgroups 9, 10, and 11 switching parameters, if not provided in table I, shall be designated by device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be maintained under document revision level control, and shall be made available to the acquiring or preparing activity upon request.

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4.2.1 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Constant acceleration method 2001 of MIL-STD-883 shall be performed to condition B for devices built with case outline Y, and condition D for devices built with case outline X.
- c. Binning program performed prior to burn-in.
- d. Interim and final electrical test parameters shall be as specified in table IIA herein.
- e. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- f. Additional screening for devices 03, 04, 07, 08, 09 and 10 shall include:
 - (1) 100% Internal visual, TM 2010 condition A
 - (2) 100% PIND (PIND is included for all devices (01 through 10))
 - (3) Serialization (Serialization is included for all devices (01 through 10))
 - (4) Static Burn-in, delta, read and record, PDA (3% functional)
 - (5) Temperature Cycles increased from 10 to 50 cycles for device types 09 and 10
 - (6) For device types 09 and 10; Pre/Post Burn-in electrical test with Read-and-Record data collection is done at room temperature (+25C). Final electrical tests with Read-and-Record data collection is done at all 3 subgroup test temperatures (-55°C, +25°C, +125°C)
 - (7) Data Package with DPA report for device types 09 and 10

4.3 Qualification inspection for device classes Q. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Qualification inspection for all devices (01 to 10) complies with class Q level requirements only.

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Conformance inspection for device 03, 04, 07, and 08 comply with class Q level requirement only, wafer lot specific group C inspection may be conducted under contract with acquiring activities.

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4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 5 and 6 of table I of method 5005 of MIL-STD-883 shall be omitted.
- c. Subgroup 4 ($C_{I/O}$ and C_{CLK}) shall be measured only for initial qualification and after any process or design changes which may affect input or output capacitance. Capacitance shall be measured between the designated terminal and GND at a frequency equal or less than 1 MHz. Sample size is on a minimum of three devices with no failures on a minimum of five worst case pins from each device.
- d. O/V (latch-up) tests shall be measured only for initial qualification and after any design or process changes which may affect the performance of the device. For device classes Q and V, the procedures and circuits shall be under the control of the device manufacturer's technical review board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the preparing activity or acquiring activity upon request. Testing shall be on all pins, on a minimum of three devices with zero failures. Latch-up test shall be considered destructive. Information contained in JEDEC JESD 78 may be used for reference.
- e. Programmed device (see 3.2.3.2) - For device classes Q and V, subgroups 7, 8A, and 8B shall include verifying the functionality of the device. These tests shall have been fault graded in accordance with MIL-STD-883, method 5012.
- f. Unprogrammed devices shall be tested for programmability and dc and ac performance compliance to the requirements of group A, subgroups 1 and 7 (Note: The following steps are done prior to burn-in).
 - (1) Programming requirements shall be based on either wafer lot or assembly lot. An assembly lot is comprised of one or more wafers from the wafer lot. Sample size series shall be 8 devices with no programming failures. The occurrence of one programming failure will allow for an additional 5 samples to be tested with no additional programming failures allowed 13 (1). The occurrence of a second programming failure will allow for an additional 5 samples to be tested with no additional programming failures allowed 18(2). The occurrence of more than 3 programming failures during this process allows the manufacture to resubmit to a tightened sample size series of 48(3) or 85(7).
 - (2) Retesting of devices due to failure shall be in accordance the device manufacturer's Quality Management (QM) plan for the purpose of determining the failure as True or False as defined in the device manufacturer's Quality Management (QM) plan.
 - (3) All units that have passed programming shall be tested for functionality. The occurrence of one DC failure at functional testing shall require the manufacture to perform 100% electrical testing of the assembly or wafer lot followed by a functional test using a sample size series of 45(minimum) programmed devices with no failures. The assembly or wafer lot shall be rejected if there are functional failures or more than one DC failure.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

- a. $T_A = +125^{\circ}C$, minimum.
- b. Test duration: 1,000 hours for class Q device types 1-8 and 2000 hours for class Q device types 9 and 10.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

- a. Constant acceleration method 2001 of MIL-STD-883 shall be performed to condition B for devices built with case outline Y, and condition D for devices built with case outline X.

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4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^{\circ}\text{C} \pm 5^{\circ}\text{C}$, after exposure, to the subgroups specified in table IIA herein.

4.4.5 Additional conformance inspection criteria for device classes Q and V. For device types 09 and 10, 2 set-up units at wire bond process step for each assembly lot will undergo bake for 1 hour at 300°C prior to destructive bond pull strength test, 3 grams limit minimum, on all bond wires (100%) with 0 failures in accordance with method 2011 of MIL-STD-883.

4.5 Delta measurements for device class V. Delta measurements, as specified in table IIA, shall be made and recorded before and after the required burn-in screens and steady-state life tests to determine delta compliance. The electrical parameters to be measured, with associated delta limits are listed in table IIB. The device manufacturer may, at his option, either perform delta measurements or within 24 hours after burn-in perform final electrical parameter tests, subgroups 1, 7, and 9.

TABLE IIB. Delta limits at +25°C for burn-in and lifetest.

Parameter ^{1/}	Device types	
	01, 02, 03, 04	05, 06, 07, 08, 09, 10
I_{CC}	± 2 mA of measured value in table I	± 5 mA of measured value in table I
I_{OZ}	± 5 μ A of measured value in table I	± 5 μ A of measured value in table I
t_{PBLH}, t_{PBHL}	± 10 ns	± 10 ns

^{1/} The above parameter shall be recorded before and after the required burn-in and life tests to determine the delta (Δ).

4.6 Programming procedures. The programming procedures shall be as specified by the device manufacturer and shall be made available upon request.

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5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-8108.

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

6.7 Design characteristics. The complexity of the devices covered by this document may require the user/designer to be familiar with additional design characteristics of the device. Contact the manufacturer for design and functional support. Updated versions of device manufacturer's software, device data sheet, IBIS models, and application notes may be obtained directly from device manufacturer's website.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 14-01-06

Approved sources of supply for SMD 5962-01515 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at <http://www.landandmaritime.dla.mil/Programs/Smcr/>.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962-0151501QXC	<u>3/</u>	RT54SX72S-CQ256B
5962-0151501QYC	<u>3/</u>	RT54SX72S -CQ208B
5962-0151502QXC	<u>3/</u>	RT54SX72S -1CQ256B
5962-0151502QYC	<u>3/</u>	RT54SX72S -1CQ208B
5962-0151503QXC	<u>3/</u>	RT54SX72S -CQ256E
5962-0151503QYC	<u>3/</u>	RT54SX72S -CQ208E
5962-0151504QXC	<u>3/</u>	RT54SX72S -1CQ256E
5962-0151504QYC	<u>3/</u>	RT54SX72S -1CQ208E
5962-0151505QXC	0J4Z0	RTSX72SU-CQ256B
5962-0151505QYC	0J4Z0	RTSX72SU-CQ208B
5962-0151506QXC	0J4Z0	RTSX72SU-1CQ256B
5962-0151506QYC	0J4Z0	RTSX72SU-1CQ208B
5962-0151507QXC	0J4Z0	RTSX72SU-CQ256E
5962-0151507QYC	0J4Z0	RTSX72SU-CQ208E
5962-0151508QXC	0J4Z0	RTSX72SU-1CQ256E
5962-0151508QYC	0J4Z0	RTSX72SU-1CQ208E
5962-0151509QXC	0J4Z0	RTSX72SU-CQ256EV
5962-0151509QYC	0J4Z0	RTSX72SU-CQ208EV
5962-0151510QXC	0J4Z0	RTSX72SU-1CQ256EV
5962-0151510QYC	0J4Z0	RTSX72SU-1CQ208EV

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available from an approved source.

STANDARD MICROCIRCUIT DRAWING BULLETIN – Continued.

DATE: 14-01-06

<u>number</u>	Vendor CAGE	Vendor name <u>and address</u>
0J4Z0		Actel Corporation 3870 North First Street San Jose, CA 95134-1702

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.